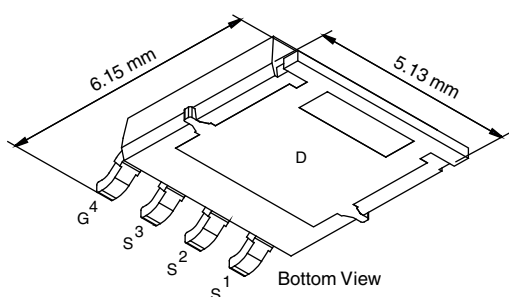


N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A)	Q_g (Typ.)
60	0.0080 at $V_{GS} = 10$ V	46.5	9.3 nC
	0.0100 at $V_{GS} = 6$ V	41.6	
	0.0125 at $V_{GS} = 4.5$ V	37.2	

PowerPAK® SO-8L



Ordering Information:
SiJ462DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

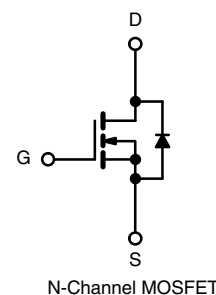
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Material categorization:
For definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Primary Side Switching
- Synchronous Rectification
- DC/DC Converters
- Boost Converters
- DC/AC Inverters



ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	46.5	A
	$T_C = 70$ °C	37.2	
	$T_A = 25$ °C	18.6 ^{b, c}	
	$T_A = 70$ °C	14.9 ^{b, c}	
Pulsed Drain Current ($t = 100$ μ s)	I_{DM}	100	A
Continuous Source-Drain Diode Current	$T_C = 25$ °C	28.3	
	$T_A = 25$ °C	4.5 ^{b, c}	
Single Pulse Avalanche Current	I_{AS}	20	mJ
Single Pulse Avalanche Energy	E_{AS}	20	
Maximum Power Dissipation	$T_C = 25$ °C	31.2	W
	$T_C = 70$ °C	20	
	$T_A = 25$ °C	5 ^{b, c}	
	$T_A = 70$ °C	3.2 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, b}	R_{thJA}	20	25	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	3	4	

Notes:

a. Maximum under steady state conditions is 70 °C/W.

b. Surface mounted on 1" x 1" FR4 board.

c. $t = 10$ s.

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	60			V	
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		97		mV/°C	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5.1			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.4		2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μA	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 55 °C			10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30			A	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0065	0.0080	Ω	
		V _{GS} = 6 V, I _D = 15 A		0.0080	0.0100		
		V _{GS} = 4.5 V, I _D = 10 A		0.0100	0.0125		
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 20 A		80		S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz		1400		pF	
Output Capacitance	C _{oss}			525			
Reverse Transfer Capacitance	C _{rss}			45			
Total Gate Charge	Q _g	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 10 A		20.8	32	nC	
		V _{DS} = 30 V, V _{GS} = 6 V, I _D = 10 A		12.1	18.5		
	V _{DS} = 30 V, V _{GS} = 4.5 V, I _D = 10 A		9.3	14			
		Gate-Source Charge	Q _{gs}		4.1		
		Gate-Drain Charge	Q _{gd}		2.3		
	Output Charge	Q _{oss}	V _{DS} = 30 V, V _{GS} = 0 V		23.5		36
Gate Resistance	R _g	f = 1 MHz	0.8	2.3	3.7	Ω	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 30 V, R _L = 3 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω		10	20	ns	
Rise Time	t _r			10	20		
Turn-Off Delay Time	t _{d(off)}			24	48		
Fall Time	t _f			8	16		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 30 V, R _L = 3 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω		25	50		
Rise Time	t _r			50	100		
Turn-Off Delay Time	t _{d(off)}			17	34		
Fall Time	t _f			9	18		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			28.3	A	
Pulse Diode Forward Current (t _p = 100 μs)	I _{SM}				100		
Body Diode Voltage	V _{SD}	I _S = 5 A		0.77	1.1	V	
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C		25	50	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			16	32	nC	
Reverse Recovery Fall Time	t _a			14		ns	
Reverse Recovery Rise Time	t _b			11			

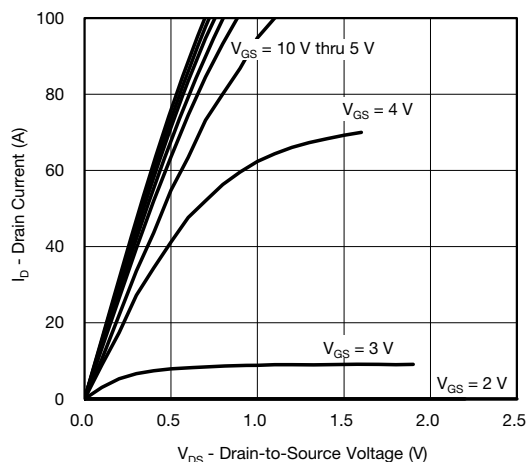
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

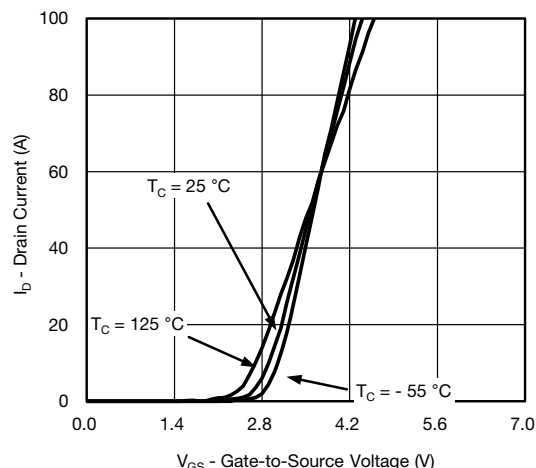
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

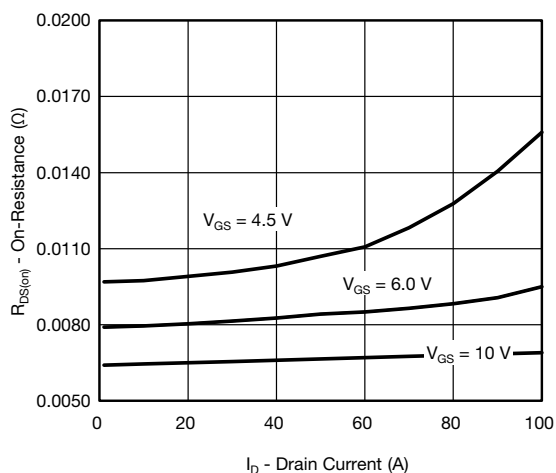
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



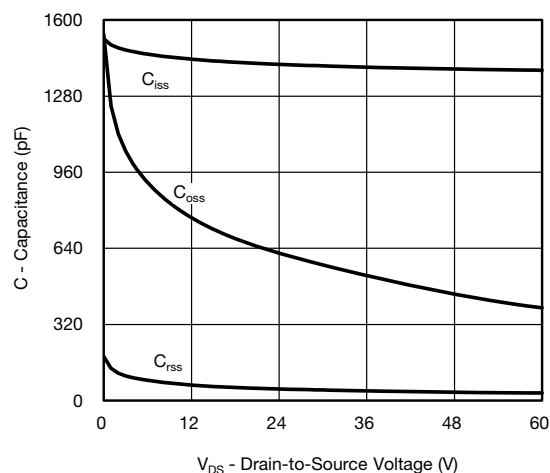
Output Characteristics



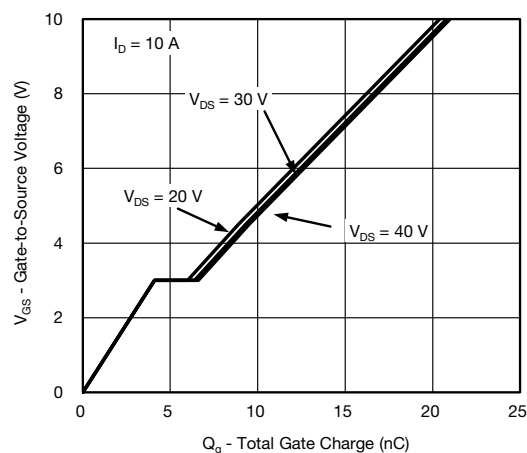
Transfer Characteristics



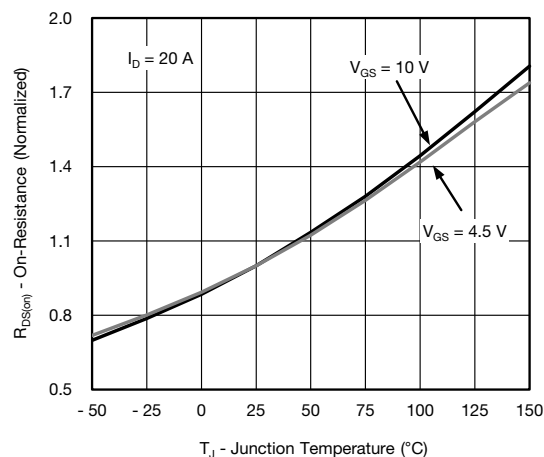
On-Resistance vs. Drain Current



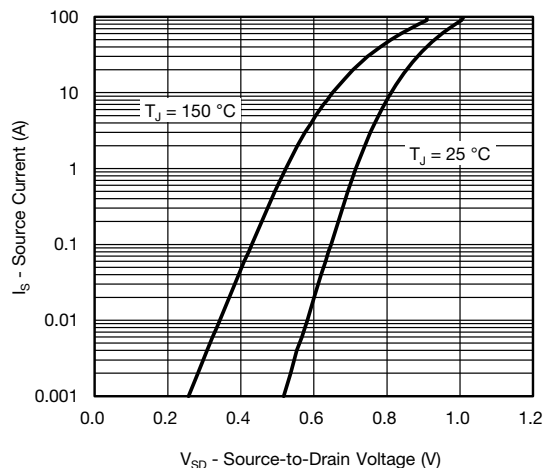
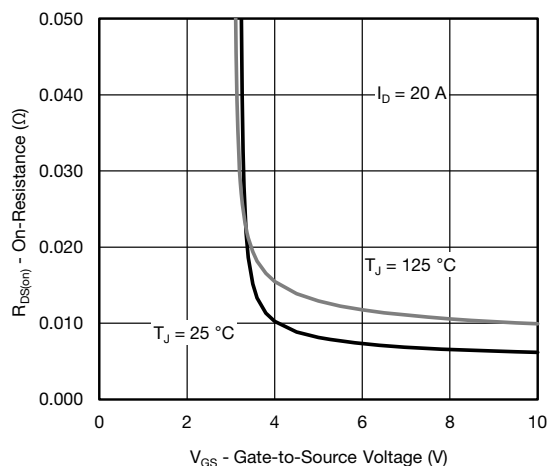
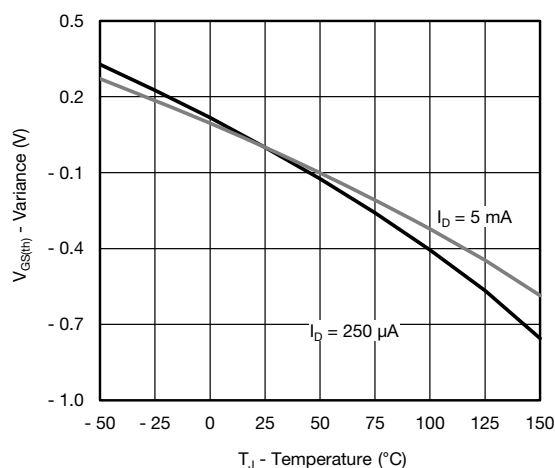
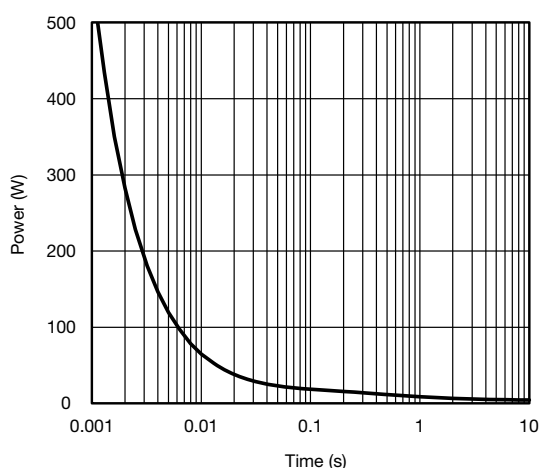
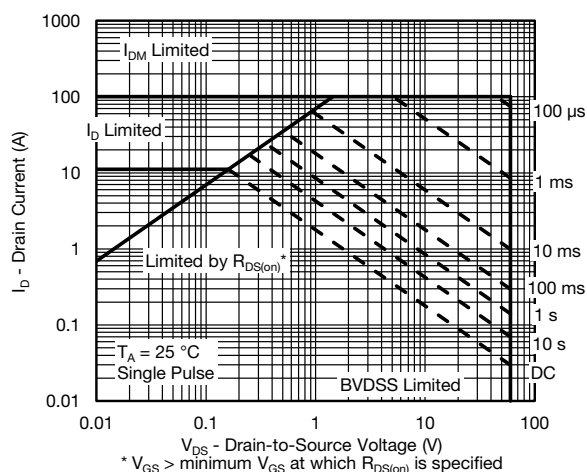
Capacitance



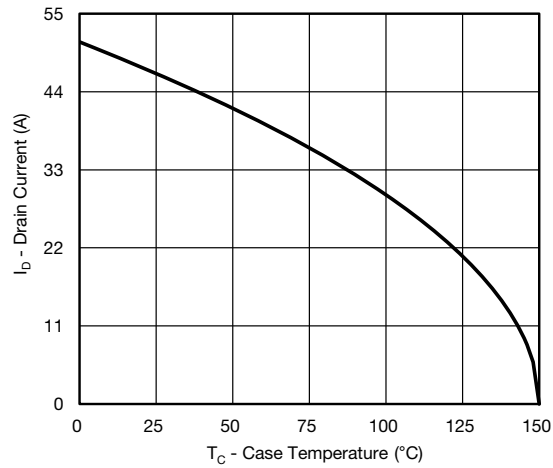
Gate Charge



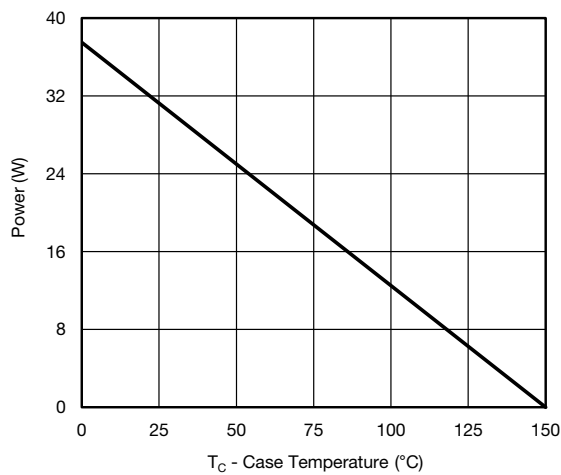
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient****Safe Operating Area, Junction-to-Ambient**

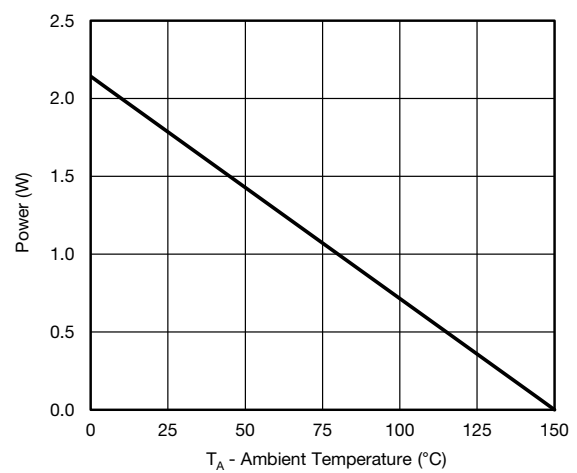
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*

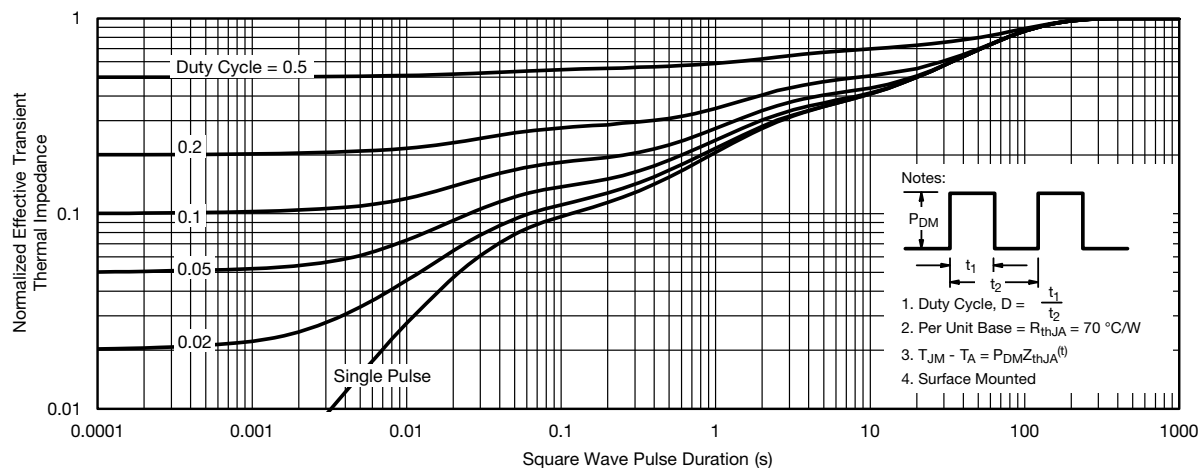
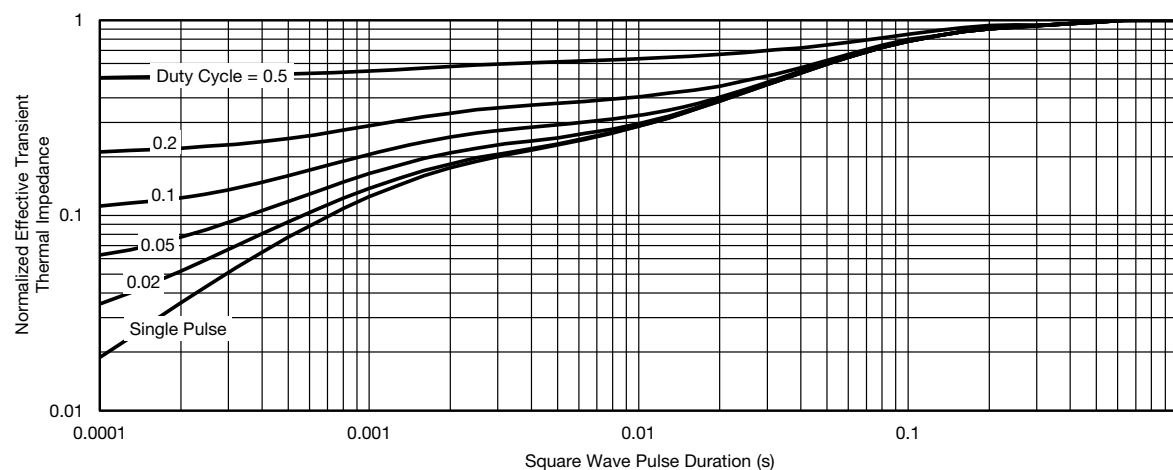


Power, Junction-to-Case



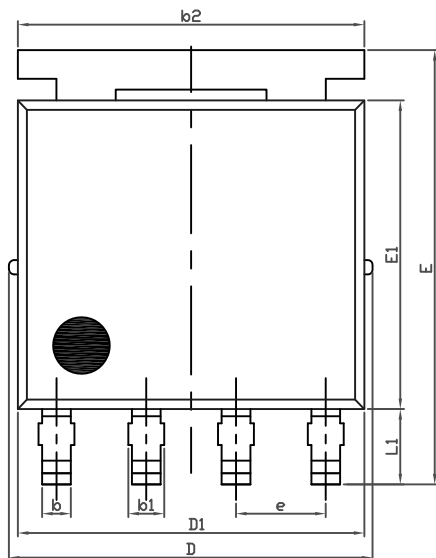
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

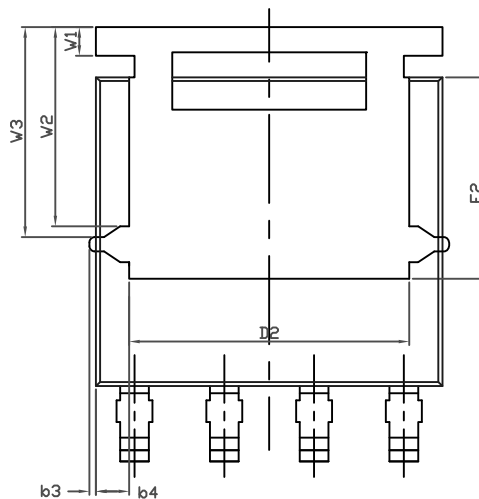
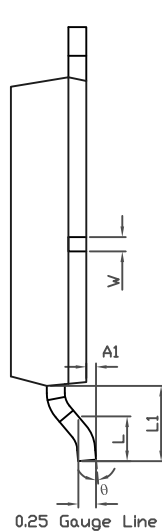
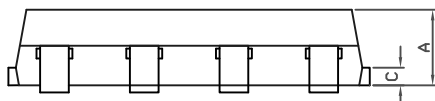
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62871.

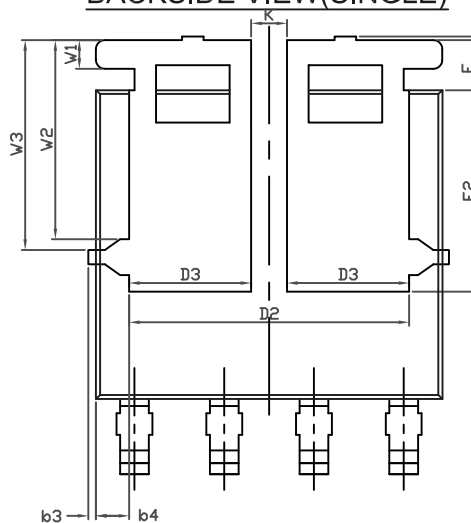
PowerPAK® SO-8L Case Outline



TOPSIDE VIEW



BACKSIDE VIEW(SINGLE)



BACKSIDE VIEW(DUAL)



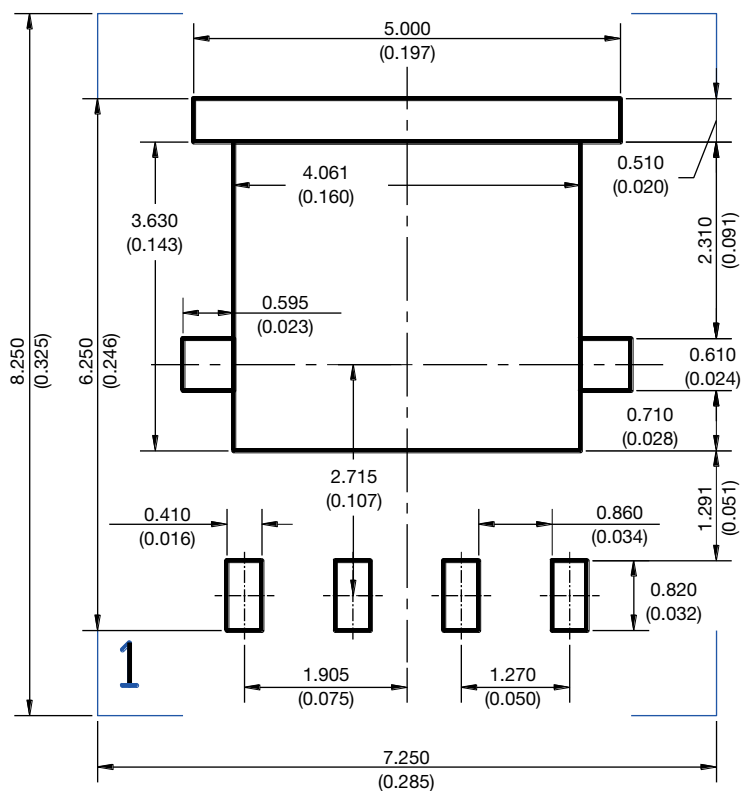
DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.094			0.004		
b4	0.47			0.019		
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2 (for AI product)	2.75	2.85	2.95	0.108	0.112	0.116
E2 (for other product)	3.18	3.28	3.38	0.125	0.129	0.133
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.51			0.020		
W	0.23			0.009		
W1	0.41			0.016		
W2	2.82			0.111		
W3	2.96			0.117		
θ	0°	-	10°	0°	-	10°
ECN: C12-0026-Rev. B, 27-Aug-12 DWG: 5976						

Note

- Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads
Dimensions in mm (inches)



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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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